

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

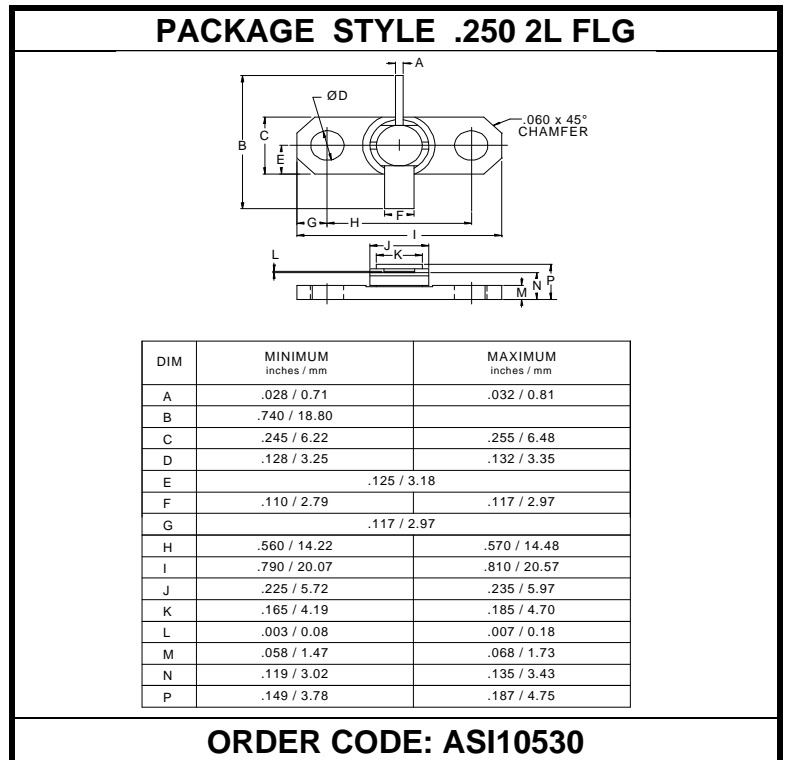
The **ASI 2010** is Designed for General Purpose Class C Power Amplifier Applications up to 2300 MHz.

**FEATURES:**

- $P_G = 5$  dB min. at 10 W/ 2,000 MHz
- Hermetic Microstrip Package
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

|               |                                 |
|---------------|---------------------------------|
| $I_C$         | 1.5 A                           |
| $V_{CC}$      | 35 V                            |
| $P_{DISS}$    | 35 W @ $T_C = 25^\circ C$       |
| $T_J$         | $-65^\circ C$ to $+200^\circ C$ |
| $T_{STG}$     | $-65^\circ C$ to $+200^\circ C$ |
| $\theta_{JC}$ | 5.0 $^\circ C/W$                |


**CHARACTERISTICS**  $T_C = 25^\circ C$ 

| SYMBOL     | TEST CONDITIONS                                | MINIMUM | TYPICAL | MAXIMUM | UNITS |
|------------|--|---------|---------|---------|-------|
| $BV_{CBO}$ | $I_C = 5$ mA                                   | 45      |         |         | V     |
| $BV_{CER}$ | $I_C = 15$ mA $R_{BE} = 10 \Omega$             | 45      |         |         | V     |
| $BV_{EBO}$ | $I_E = 1$ mA                                   | 3.5     |         |         | V     |
| $I_{CBO}$  | $V_{CB} = 28$ V                                |         |         | 5.0     | mA    |
| $h_{FE}$   | $V_{CE} = 5.0$ V $I_C = 1000$ mA               | 15      |         | 120     | ---   |
| $C_{ob}$   | $V_{CB} = 28$ V $f = 1.0$ MHz                  |         |         | 7.5     | pF    |
| $P_G$      | $V_{CC} = 28$ V $P_{OUT} = 10$ W $f = 2.0$ GHz | 5.0     |         |         | dB    |
| $\eta_c$   |  | 35      |         |         | %     |